

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO. 03500.013395.2		APPLICATION NO. Div. of 09/839,891	
				APPLICANT KEISHI SAITO ET AL.			
				FILING DATE H rewith		GROUP NYA	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
M	4,600,801	7/15/86	Guha et al.	136	249		
	4,609,771	9/2/86	Guha et al.	136	249		
	4,775,425	10/4/88	Guha et al.	136	249		
	5,486,237	1/23/96	Sano et al.	136	258		
	5,720,827	2/24/98	Simmons	136	250		
	5,851,904	12/22/98	Schwarz et al.	438	482		
	5,913,986	6/22/99	Matsuyama	136	255		
19	6,013,544	1/11/00	Makita et al.	438	166		

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT		
21	0 675 551	10/4/95	Europe				
	43 33 416	4/6/95	Germany				

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<div style="text-align: center;">14</div>	J. Meier, et al., "Towards High Efficiency Thin Film Silicon Solar Cells With The 'Micromorph' Concept", Solar Energy Materials and Solar Cells, vol. 49, pp. 35-44 (1997).
	J. Yi, et al., "Amorphous and Micro-Crystalline Silicon for Photovoltaic Application", Proc. of the Photovoltaic Spec. Conf., vol. 23, pp. 977-980 (1993).
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	A. Matsuda, "Structural Study on Amorphous-Microcrystalline Mixed-Phase Si:H Films", Jap. J. Appl. Phys., vol. 20, no. 6, pgs. L439-L442 (1981).
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<div style="text-align: center;">14</div>	A. Matsuda, et al. "Electrical and Structural Properties of Phosphorous-Doped Glow-Discharge Si: F: H and Si:H Films", Jap. J. Appl. Phys., vol. 19, no. 6, pgs. L305-L308 (1980).
	S. Usui, et al., "Properties of Heavily Doped GD-Si With Low Resistivity", Journal of Non-Crystalline Solids, vol. 34, no. 1, pgs. 1-11 (1979).

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	3/18/05

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
/	6,020,224	2/1/00	Shimogaichi et al.	438	158		
/	6,027,987	2/22/00	Yamazaki et al.	438	486		
P	6,033,940	3/7/00	Jinda	438	151		
/	6,180,870	1/30/01	Sano et al.	136	258		

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/	1175095A	3/4/98	China				

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	3/15/08

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